

High Voltage Transistor

PNP Silicon

MMBT5401W

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

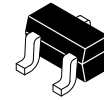
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-150	Vdc
Collector – Base Voltage	V_{CBO}	-160	Vdc
Emitter – Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I_C	-500	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

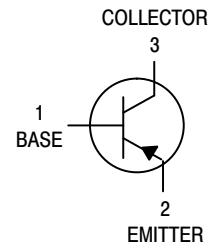
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 2) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	400	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	312	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

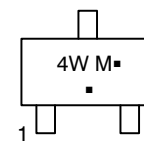
1. FR-5 @ 100 mm², 0.5 oz. copper traces, still air.
2. FR-5 = 1.0 × 0.75 × 0.062 in.



SC-70 (SOT-323)
CASE 419
STYLE 3



MARKING DIAGRAM



4W = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT5401WT1G, NSVMMBT5401WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT5401W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = –1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	–150	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = –100 µA _{dc} , I _E = 0)	V _{(BR)CBO}	–160	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = –10 µA _{dc} , I _C = 0)	V _{(BR)EBO}	–5.0	–	V _{dc}
Collector–Base Cutoff Current (V _{CB} = –120 V _{dc} , I _E = 0) (V _{CB} = –120 V _{dc} , I _E = 0, T _A = 100°C)	I _{CBO}	– –	–50 –50	nA _{dc} µA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = –1.0 mA _{dc} , V _{CE} = –5.0 V _{dc}) (I _C = –10 mA _{dc} , V _{CE} = –5.0 V _{dc}) (I _C = –50 mA _{dc} , V _{CE} = –5.0 V _{dc})	h _{FE}	50 60 50	– 240 –	–
Collector–Emitter Saturation Voltage (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{CE(sat)}	– –	–0.2 –0.5	V _{dc}
Base–Emitter Saturation Voltage (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{BE(sat)}	– –	–1.0 –1.0	V _{dc}

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I _C = –10 mA _{dc} , V _{CE} = –10 V _{dc} , f = 100 MHz)	f _T	100	300	MHz
Output Capacitance (V _{CB} = –10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	–	6.0	pF
Small Signal Current Gain (I _C = –1.0 mA _{dc} , V _{CE} = –10 V _{dc} , f = 1.0 kHz)	h _{fe}	40	200	–
Noise Figure (I _C = –200 µA _{dc} , V _{CE} = –5.0 V _{dc} , R _S = 10 Ω, f = 1.0 kHz)	NF	–	8.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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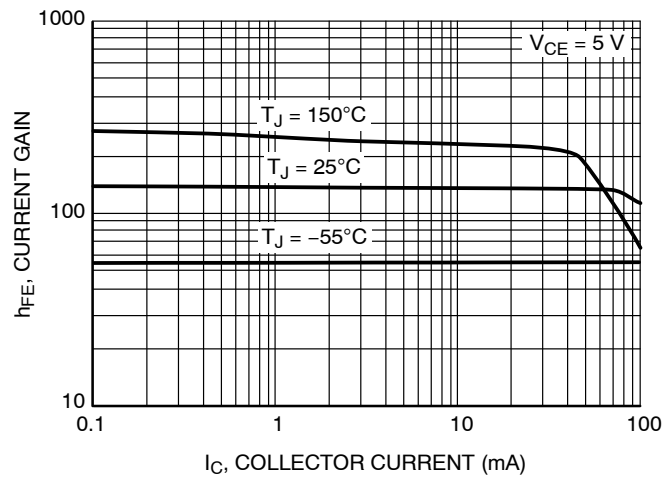


Figure 1. DC Current Gain

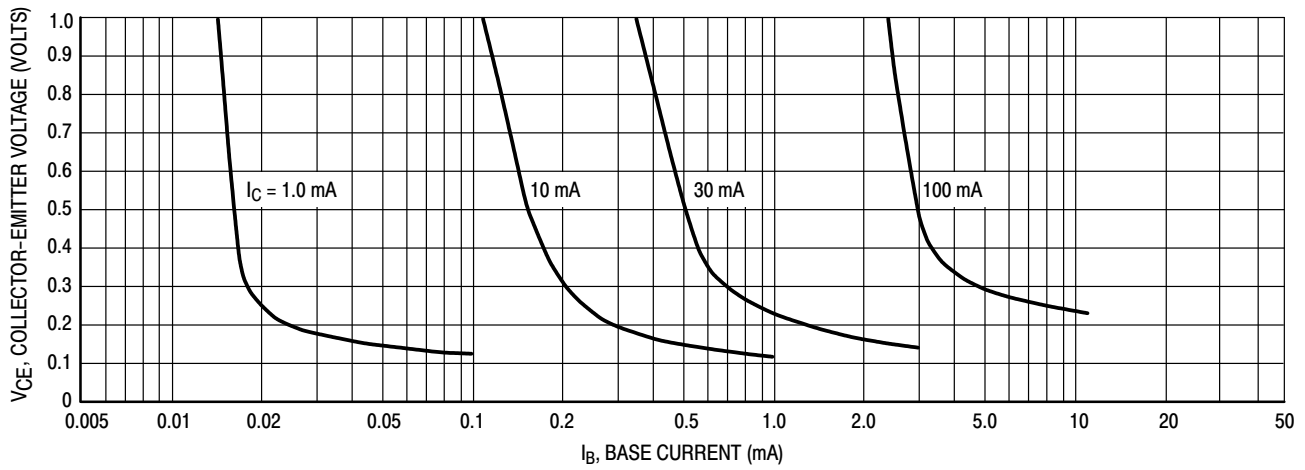


Figure 2. Collector Saturation Region

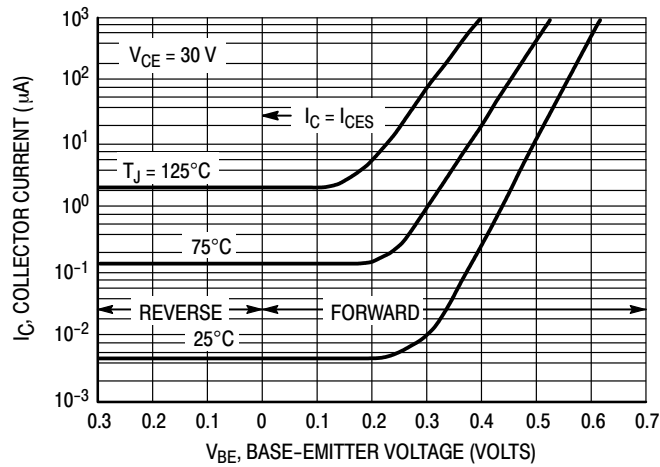


Figure 3. Collector Cut-Off Region

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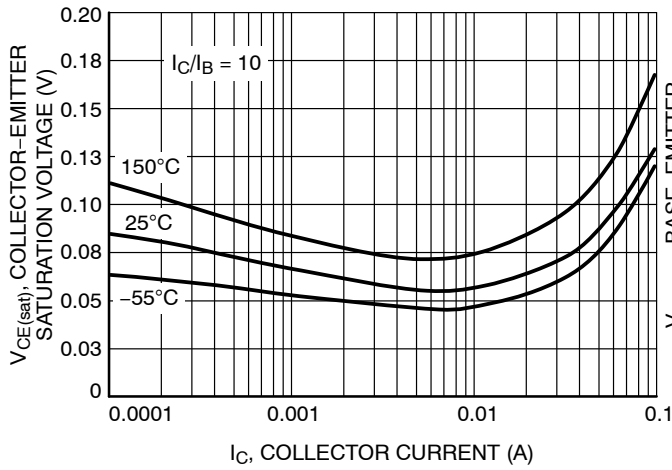


Figure 4. Collector-Emitter Saturation Voltage vs. Collector Current

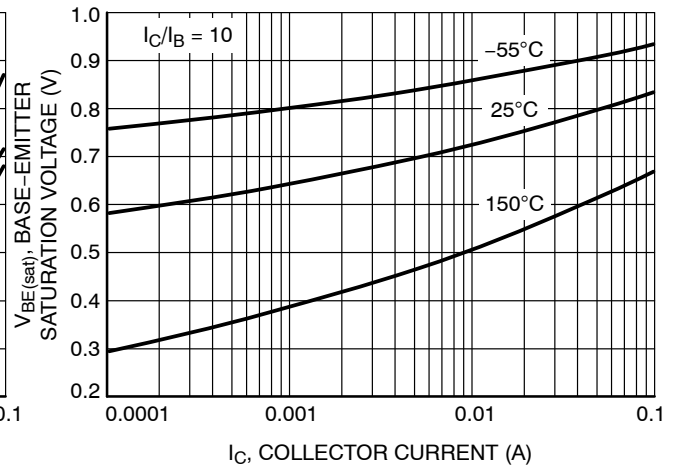


Figure 5. Base-Emitter Saturation Voltage vs. Collector Current

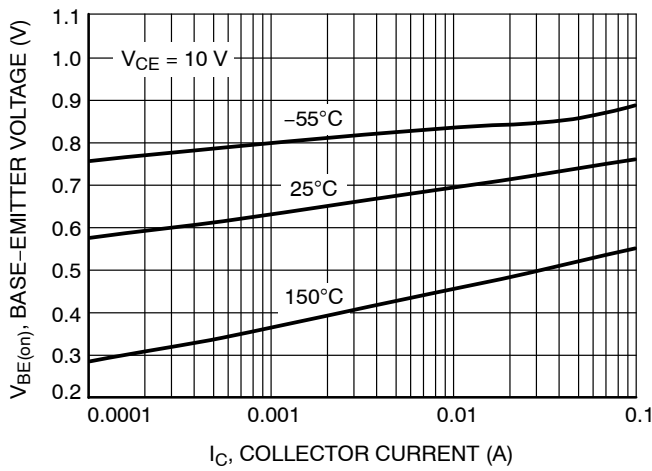


Figure 6. Base-Emitter Voltage vs. Collector Current

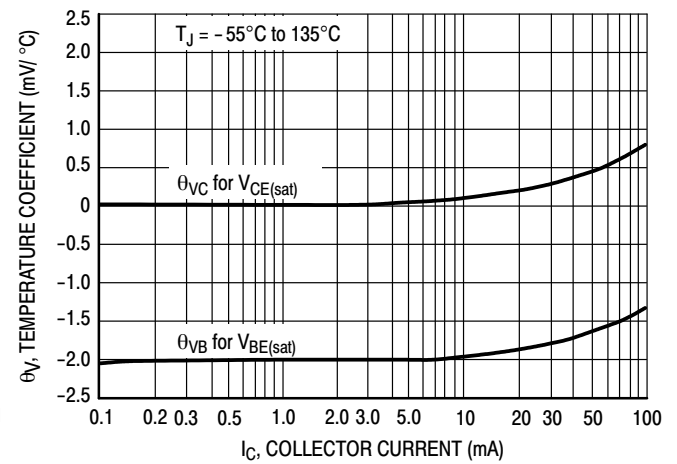
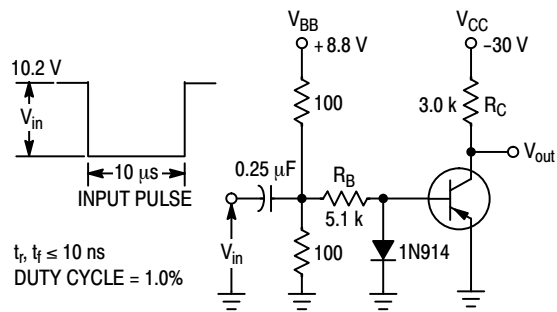


Figure 7. Temperature Coefficients



Values Shown are for I_C @ 10 mA

Figure 8. Switching Time Test Circuit

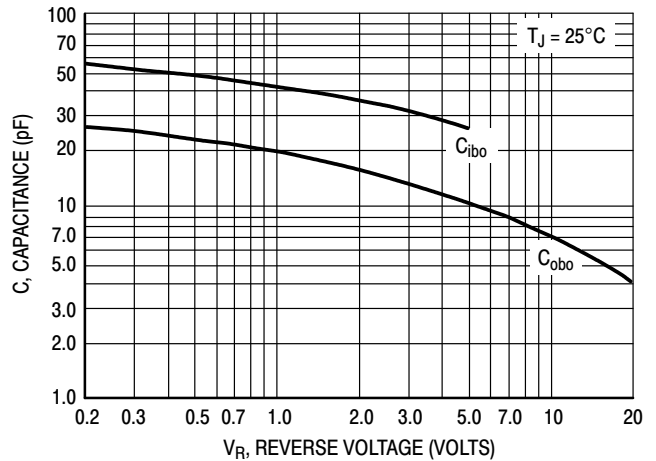


Figure 9. Capacitances

MMBT5401W

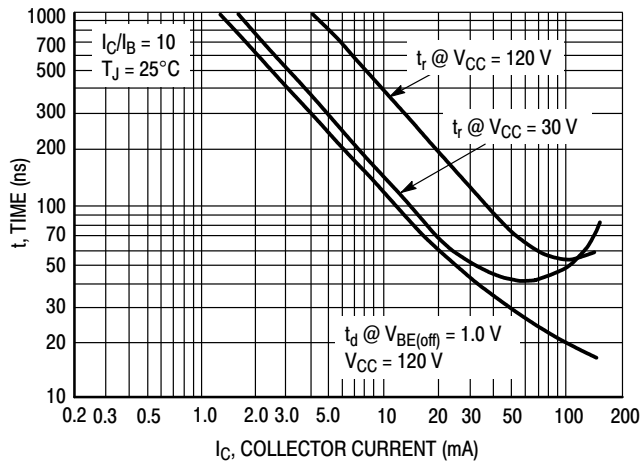


Figure 10. Turn-On Time

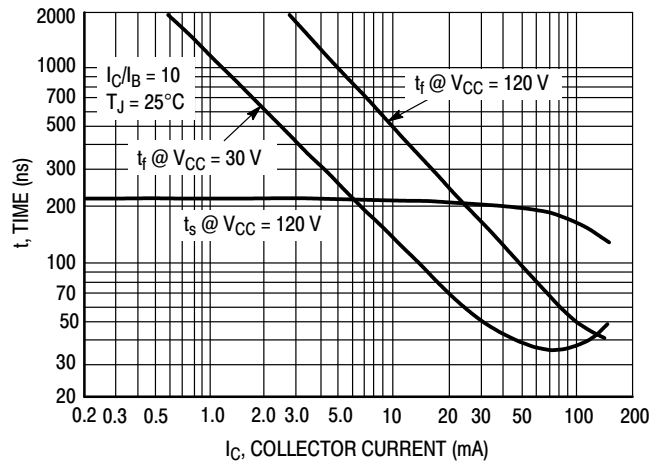


Figure 11. Turn-Off Time

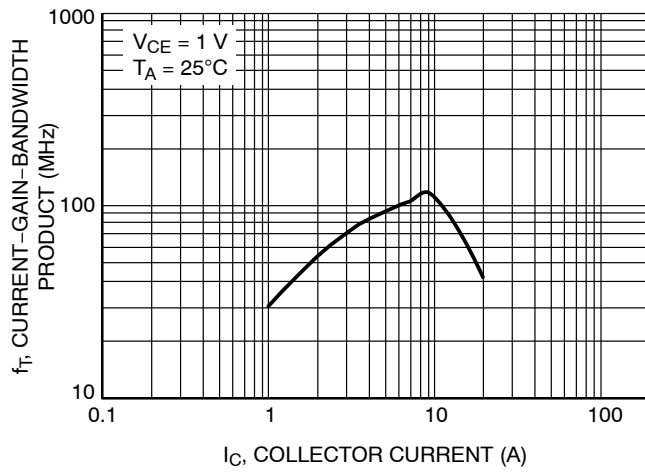


Figure 12. Current Gain Bandwidth Product

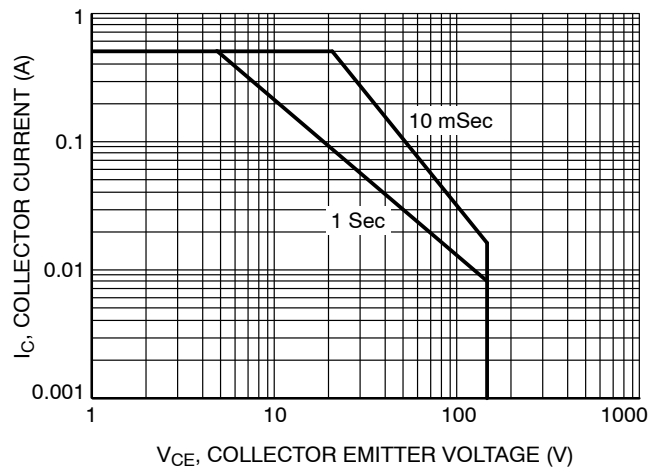


Figure 13. Safe Operating Area



SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE R

DATE 11 OCT 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC
MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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